

Substitute for form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	10/524,809
Filing Date	02/15/2005
Inventor(s)	James S. Im
Art Unit	2895
Examiner Name	Fernando L. Toledo
Attorney Docket Number	070050.2721

U.S. PATENT DOCUMENTS

Exam Initial	No.	Document No.	Publication Date	Applicant(s)
	1.	4514895	5/7/1985	Nishimura, Tadashi
	2.	4976809	12/11/1990	Broadbent, Eliot K.
	3.	5413958	5/9/1995	Imahashi, Issei ; Hama, Kiichi ; Hata, Jiro
	4.	5417897	5/23/1995	Asakawa, Stuart D. ; McClelland, Paul H. ; Tappon, Ellen R. ; Vandepoll, Richard R. ; Trueba, Kenneth E. ; Chen, Chien Hua
	5.	5436095	7/25/1995	Mizuno, Fumio ; Moriuchi, Noboru ; Shirai, Seiichiro ; Morita, Masayuki
	6.	5466908	11/14/1995	Hosoya, Kimio ; Teruya, Yoshihiro ; Kobayashi, Yasushi
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	8.	5614421	3/25/1997	Yang, Sheng Hsing
	9.	5614426	3/25/1997	Funada, Fumiaki ; Morita, Tatsuo ; Tanaka, Hirohisa ; Zhang, Hongyong ; Takayama, Toru
	10.	5616506	4/1/1997	Takemura, Yasuhiko
	11.	5620910	4/15/1997	Teramoto, Satoshi
	12.	5710050	1/20/1998	Makita, Naoki ; Miyamoto, Tadayoshi
	13.	5736709	4/7/1998	Neiheisel, Gary L.

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	14.	6093934	7/25/2000	Yamazaki, Shunpei ; Teramoto, Satoshi ; Koyama, Jun ; Ogata, Yasushi ; Hayakawa, Masahiko ; Osame, Mitsuaki ; Ohtani, Hisashi ; Hamatani, Toshiji
	15.	6117301	9/12/2000	Freudenberger, Renate ; Zielonka, Andreas
	16.	6198141	3/6/2001	Yamazaki, Shunpei ; Ohtani, Hisashi ; Fukunaga, Takeshi
	17.	6222195	4/24/2001	Yamada, Akio ; Sagou, Satoru ; Watanabe, Hitoshi ; Yamazaki, Satoru ; Sakamoto, Kiichi ; Ohno, Manabu ; Kawakami, Kenichi ; Kobayashi, Katsuhiko
	18.	6255146	7/3/2001	Shimizu, Satoshi ; Ueno, Shuichi ; Maeda, Shigenobu ; Ipposhi, Takashi
	19.	6274488	8/14/2001	Talwar, Somit ; Wang, Yun
	20.	6341042	1/22/2002	Matsunaka, Shigeki ; Fujihara, Atsushi ; Kakuno, Tsutomu
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	22.	6353218	3/5/2002	Yamazaki, Shunpei ; Tanaka, Koichiro
	23.	6358784	3/19/2002	Zhang, Hongyong ; Yamazaki, Shunpei ; Takemura, Yasuhiko
	24.	6388386	5/14/2002	Kunii, Masafumi ; Takatoku, Makoto ; Mano, Michio

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	25.	6392810	5/21/2002	Tanaka, Koichiro
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	29.	6432758	8/13/2002	Cheng, Huang Chung ; Lin, Ching Wei ; Cheng, Li Jing
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	33.	6455359	9/24/2002	Yamazaki, Shunpei ; Teramoto, Satoshi ; Kusumoto, Naoto ; Fukunaga, Takeshi ; Nakajima, Setsuo ; Miyamoto, Tadayoshi ; Yoshinouchi, Atsushi
	34.	6471772	10/29/2002	Tanaka, Koichiro
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	38.	6493042	12/10/2002	Bozdagi, Gozde ; Yu, Hong Heather ; Harrington, Steven J. ; Bryll, Robert
	39.	6495405	12/17/2002	Voutsas, Apostolos ; Hartzell, John W. ; Nakata, Yukihiko
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	47.	6563077	5/13/2003	Im, James S.
	48.	6573163	6/3/2003	Voutsas, Apostolos ; Hartzell, John W. ; Nakata, Yukihiko
	49.	6577380	6/10/2003	Sposili, Robert S. ; Farmiga, Nestor O. ; Jain, Kanti

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	52.	6635932	10/21/2003	Grigoropoulos, Costas P. ; Hatano, Mutsuko ; Lee, Ming Hong ; Moon, Seung Jae
	53.	6660575	12/9/2003	Zhang, Hongyong
	54.	6667198	12/23/2003	Shimoto, Shigeyuki ; Uchikoga, Shuichi
	55.	6693258	2/17/2004	Sugano, Yukiyasu ; Fujino, Masahiro ; Mano, Michio ; Asano, Akihiko ; Ino, Masumitsu ; Urazono, Takenobu ; Takatoku, Makoto
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	57.	6767804	7/27/2004	Crowder, Mark Albert
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	60.	6858477	2/22/2005	Deane, Steven C. ; French, Ian D.
	61.	6908835	6/21/2005	Sposili, Robert S. ; Im, James S.
	62.	6961117	11/1/2005	Im, James S.
	63.	7091411	8/15/2006	Falk, Fritz ; Andrae, Gudrun

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Exam Initial	No.	Document No.	Publication Date	Applicant(s)
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	65.	7217605	5/15/2007	Kawasaki, Ritsuko ; Nakajima, Setsuo
	66.	7259081	8/21/2007	Im, James S.
	67.	7297982	11/20/2007	Suzuki, Kenkichi ; Nagata, Tetsuya ; Takahashi, Michiko ; Saito, Masakazu ; Ogino, Toshio ; Miyano, Masanobu
	68.	7300858	11/27/2007	Im, James S.
	69.	7311778	12/25/2007	Im, James S. ; van der Wilt, Paul Christiaan
	70.	7341928	3/11/2008	Im, James S.
	71.	20020083557	7/4/2002	Jung, Yun Ho
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	73.	20020119609	8/29/2002	Hatano, Mutsuko ; Yamaguchi, Shinya ; Kimura, Yoshinobu ; Park, Seong Kee
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	76.	20030006221	1/9/2003	Hong, Minghui ; Ye, Kaidong ; An, Chengwu ; Liu, Da Ming

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	77.	20030013278	1/16/2003	Jang, Jin ; Kim, Kyung, Ho
	78.	20030014337	1/16/2003	Mathews, Scott, H. ; Datar, Vinay, T.
	79.	20030068836	4/10/2003	Hongo, Mikio ; Uto, Sachio ; Nomoto, Mineo ; Nakata, Toshihiko ; Hatano, Mutsuko ; Yamaguchi, Shinya ; Ohkura, Makoto
	80.	20030119286	6/26/2003	Im, James, S. ; Sposili, Robert, S. ; Crowder, Mark, A.
	81.	20030148565	8/7/2003	Yamanaka, Hideo
	82.	20030194613	10/16/2003	Voutsas, Apostolos, T. ; Crowder, Mark, A. ; Mitiani, Yasuhiro
	83.	20040127066	7/1/2004	Jung, Yun Ho
	84.	20040140470	7/22/2004	Kawasaki, Ritsuko ; Kasahara, Kenji ; Ohtani, Hisashi
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	86.	20040182838	9/23/2004	Das, Palash, P. ; Bolliger, Bruce, E. ; Patel, Parthiv, S. ; Klene, Brian, C. ; Melcher, Paul, C. ; Saethre, Robert, B.
	87.	20040222187	11/11/2004	Lin, Kun Chih
	88.	20040224487	11/11/2004	Yang, Myoung Su
	89.	20050059265	3/17/2005	Im, James

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	90.	20050141580	6/30/2005	Partlo, William ; Das, Palash ; Hudyma, Russell ; Thomas, Michael
	91.	20050142450	6/30/2005	Jung, Yun
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	93.	20050202654	9/15/2005	Im, James
	94.	20060030164	2/9/2006	Im, James
	95.	20060102901	5/18/2006	Im, James ; van der Wilt, Paul
	96.	20060125741	6/15/2006	Tanaka, Masahiro ; Matsuura, Toshiyuki ; Murakami, Hajime ; Akimoto, Hajime
	97.	20060211183	9/21/2006	Duan, Xiangfeng ; Niu, Chunming ; Empedocles, Stephen ; Romano, Linda ; Chen, Jian ; Sahi, Vijendra ; Bock, Lawrence ; Stumbo, David ; Parce, J. ; Goldman, Jay
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	99.	20070007242	1/11/2007	Im, James
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	101.	20070032096	2/8/2007	Im, James, S.
	102.	20070108472	5/17/2007	Jeong, Jae, Kyeong ; Shin, Hyun, Soo ; Kwon, Se, Yeoul ; Mo, Yeon, Gon
	103.	20070111349	5/17/2007	Im, James

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	104.	20070215942	9/20/2007	Chen, Po Chu ; Ho, King Yuan

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	106.	DE19839718 (with English machine translation)	3/2/2000	Christiansen, Jens Ingwer, Prof. Dr. ; Christiansen, Kai, Dipl.-Phys. ; Christiansen, Silke, Dr. ; Ngendanck, Matthias, Dipl.-Phys. ; Strunk, Horst Paul, Prof. Dr.
	107.	JP4279064 (with English Abstract)	10/5/1992	UEDA TORU
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	113.	WO05029551	3/31/2005	IM, James, S. ; VAN DER WILT, Paul, Christiaan

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Application Number	10/524,809
Filing Date	02/15/2005
Inventor(s)	James S. Im
Art Unit	2895
Examiner Name	Fernando L. Toledo
Attorney Docket Number	070050.2721

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